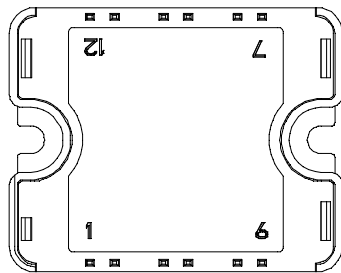
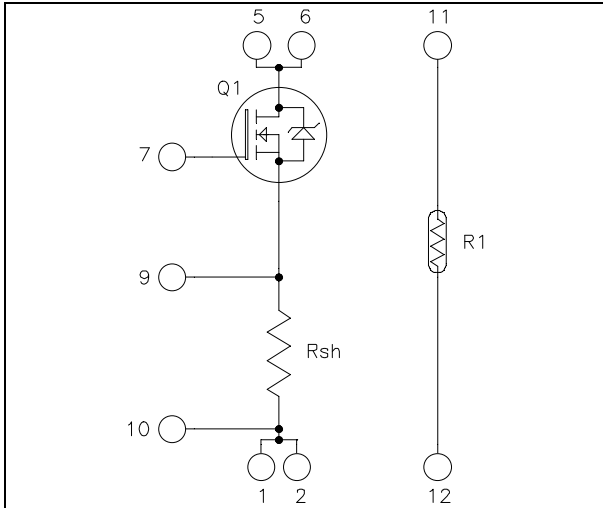


## Linear MOSFET Power Module

$V_{DSS} = 200V$   
 $R_{DSon} = 18m\Omega \text{ typ @ } T_j = 25^\circ C$   
 $I_D = 109A^* @ T_c = 25^\circ C$



Pins 1/2 ; 5/6 must be shorted together

### Application

- Electronic load dedicated to power supplies and battery discharge testing

### Features

- Linear MOSFET
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration
- AlN substrate for improved thermal performance

### Benefits

- Direct mounting to heatsink (isolated package)
- easy series and parallels combinations for power and voltage improvements
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	200	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	109*
		$T_c = 80^\circ C$	81*
$I_{DM}$	Pulsed Drain current	400	A
$V_{GS}$	Gate - Source Voltage	$\pm 30$	V
$R_{DSon}$	Drain - Source ON Resistance	19	m $\Omega$
$P_D$	Maximum Power Dissipation ❶	$T_c = 25^\circ C$	480
$I_{AR}$	Avalanche current (repetitive and non repetitive)	100	A
$E_{AR}$	Repetitive Avalanche Energy	50	mJ
$E_{AS}$	Single Pulse Avalanche Energy	3000	

\* Output current must be limited to 44A @  $T_c=25^\circ C$  and 31A @  $T_c=80^\circ C$  to not exceed the shunt specification.

❶ In saturation mode

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

### Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 200\text{V}; V_{GS} = 0\text{V}$ $T_j = 25^\circ\text{C}$			25	$\mu\text{A}$
		$V_{DS} = 160\text{V}; V_{GS} = 0\text{V}$ $T_j = 125^\circ\text{C}$			250	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 50\text{A}$		18	19	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5\text{mA}$	2		4	V
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{V}$			$\pm 100$	nA

### Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0\text{V}$ $V_{DS} = 25\text{V}$ $f = 1\text{MHz}$		9880		pF
$C_{oss}$	Output Capacitance			2320		
$C_{rss}$	Reverse Transfer Capacitance			700		

### Shunt Electrical Characteristics

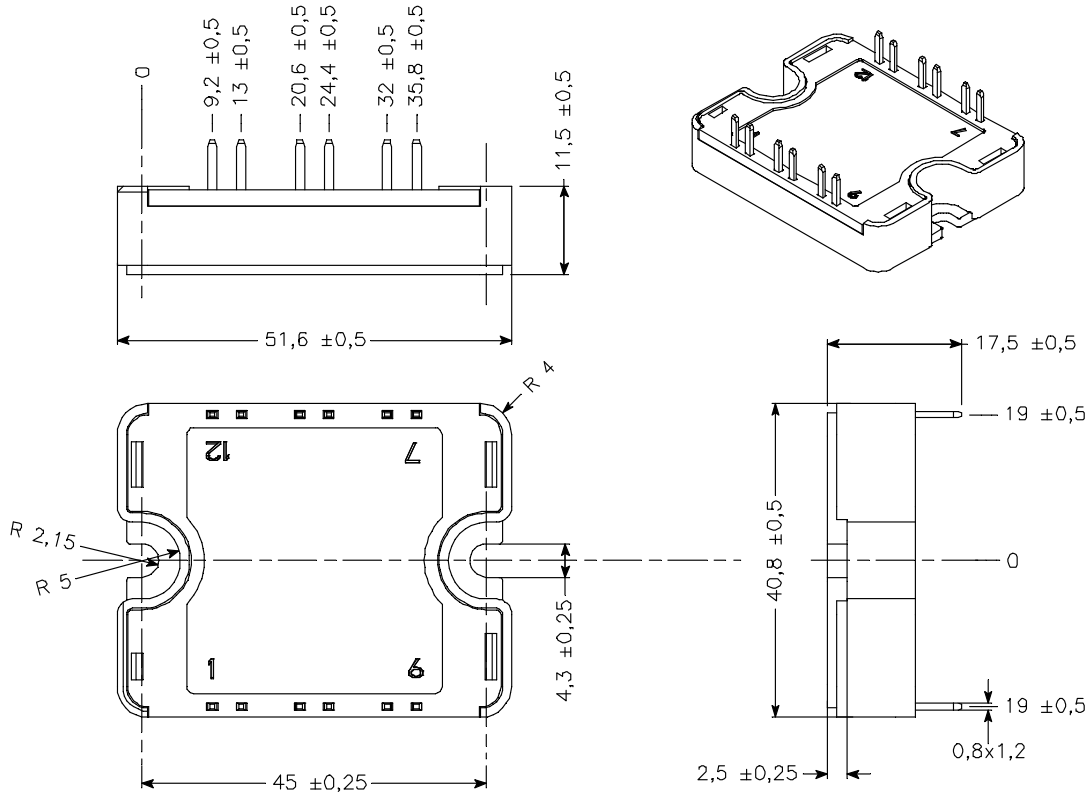
Symbol	Characteristic	Min	Typ	Max	Unit
$R_{sh}$	Resistance value		10		$\text{m}\Omega$
$T_{sh}$	Tolerance		2		%
$P_{sh}$	Load capacity	$T_C = 25^\circ\text{C}$		20	W
		$T_C = 80^\circ\text{C}$		10	
$I_{sh}$	Current capacity	$T_C = 25^\circ\text{C}$		44	A
		$T_C = 80^\circ\text{C}$		31	

### Temperature sensor PTC

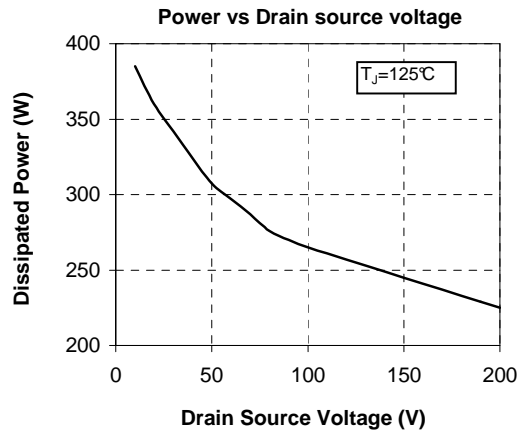
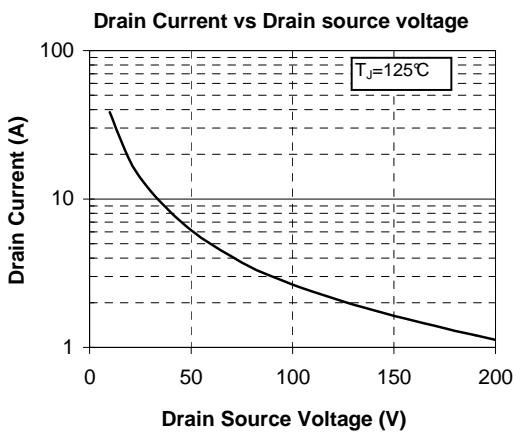
Symbol	Characteristic	Min	Typ	Max	Unit
$R_{25}$	Resistance @ $25^\circ\text{C}$	1980		2020	$\Omega$
$R_{100}/R_{25}$	Resistance ratio	$T_{amb} = 100^\circ\text{C} \& 25^\circ\text{C}$	1.676	1.696	1.716
$R_{-55}/R_{25}$	Resistance ratio	$T_{amb} = -55^\circ\text{C} \& 25^\circ\text{C}$	0.48	0.49	0.50
B	Temperature coefficient		7900		ppm/K

### Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
$R_{thJC}$	Junction to Case Thermal Resistance	MOSFET		0.26	$^\circ\text{C}/\text{W}$	
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case $t = 1\text{ min}, I_{isol} < 1\text{mA}, 50/60\text{Hz}$	4000			V	
$T_j$	Operating junction temperature range	-40		150	$^\circ\text{C}$	
$T_{STG}$	Storage Temperature Range	-40		125		
$T_C$	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight				80	g

**SP1 Package outline (dimensions in mm)**


See application note 1904 - Mounting Instructions for SP1 Power Modules on [www.microsemi.com](http://www.microsemi.com)

**Typical Performance Curve (linear mode)**


Microsemi reserves the right to change, without notice, the specifications and information contained herein

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